IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

2. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film covering a surface of the wiring;

forming a leveling film containing a siloxane structure on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film ~~; and~~

~~forming an electro-luminescence layer over the pixel electrode~~.

3. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film deposited on the wiring;

forming a leveling film containing a siloxane structure on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film~~; and~~

~~forming an electro-luminescence layer over the pixel electrode~~.

4. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the ~~insulating~~ silicon nitride oxide film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

5. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film covering a surface of the wiring;

forming a leveling film containing a siloxane structure on the silicon nitride oxide film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

6. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film deposited on the wiring;

forming a leveling film containing a siloxane structure on the ~~insulating~~ silicon nitride oxide film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second

hole formed in the silicon nitride oxide film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

7. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the ~~insulating~~ silicon nitride film;

forming a pixel electrode connecting the wiring through a second hole in the ~~insulating~~ silicon nitride film and the leveling film over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

8. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the ~~insulating~~ silicon nitride oxide film;

forming a pixel electrode connecting the wiring through a second hole in the ~~insulating~~ silicon nitride oxide film and the leveling film over the leveling film;

forming an electro luminescence layer over the pixel electrode; and

forming a cathode made of a conductive film having a light-shielding property.

9. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~first insulating~~ silicon nitride oxide film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the ~~first insulating~~ silicon nitride oxide film;

forming a pixel electrode connecting the wiring through a second hole in the ~~first insulating~~ silicon nitride oxide film and the leveling film over the leveling film;

~~forming a second insulating film over the pixel electrode;~~ and

forming an electro luminescence layer over the pixel electrode ~~and the second insulating film~~.

10. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

11. (canceled)

12. (previously presented) The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

13. (canceled)

14. (previously presented) The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. (canceled)

16. (previously presented) The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. (canceled)

18. (previously presented) The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (canceled)

20. (previously presented) The method according to claim 5, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (canceled)

22. (previously presented) The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (canceled)

24. (previously presented) The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (canceled)

26. (previously presented) The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (canceled)

28. (previously presented) The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29. (canceled)

30. (previously presented) The method according to claim 10, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

31. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film covering a surface of the wiring;

forming a leveling film formed by a spin coating method on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

32. (previously presented) The method according to claim 31, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

33. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a ~~passivation~~ silicon nitride film deposited on the wiring;

forming a leveling film formed by a spin coating method on the ~~passivation~~ silicon nitride film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

34. (Previously Presented) The method according to claim 33, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

35. (Previously Presented) The method according to claim 1, wherein the wiring is formed by a sputtering method.

36. (Previously Presented) The method according to claim 1, wherein the wiring comprises aluminum.

37. (Previously Presented) The method according to claim 1, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

38. (Currently Amended) The method according to claim 1, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

39. (Currently Amended) The method according to claim 1, wherein the ~~passivation~~ silicon nitride film has a thickness of 50 to 500nm.

40. (Currently Amended) The method according to claim 1, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

41. (Previously Presented) The method according to claim 1, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

42. (Previously Presented) The method according to claim 1, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling

film.

43. (Previously Presented) The method according to claim 1, wherein the pixel electrode is made of a conductive oxide film.

44. (Previously Presented) The method according to claim 2, wherein the wiring is formed by a sputtering method.

45. (Previously Presented) The method according to claim 2, wherein the wiring comprises aluminum.

46. (Previously Presented) The method according to claim 2, wherein the wiring is a three-layered laminate film containing a first titanium, an aluminum film and a second titanium.

47. (Currently Amended) The method according to claim 2, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

48. (Currently Amended) The method according to claim 2, wherein the ~~passivation~~ silicon nitride film has a thickness of 50 to 500nm.

49. (Currently Amended) The method according to claim 2, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

50. (Previously Presented) The method according to claim 2, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

51. (Previously Presented) The method according to claim 2, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

52. (Previously Presented) The method according to claim 2, wherein the pixel electrode is made of a conductive oxide film.

53. (Previously Presented) The method according to claim 3, wherein the wiring is formed by a sputtering method.

54. (Previously Presented) The method according to claim 3, wherein the wiring comprises aluminum.

55. (Previously Presented) The method according to claim 3, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

56. (Currently Amended) The method according to claim 3, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

57. (Currently Amended) The method according to claim 3, wherein the ~~passivation~~ silicon

nitride film has a thickness of 50 to 500nm.

58. (Currently Amended) The method according to claim 3, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

59. (Previously Presented) The method according to claim 3, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

60. (Previously Presented) The method according to claim 3, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

61. (Previously Presented) The method according to claim 3, wherein the pixel electrode is made of a conductive oxide film.

62. (Previously Presented) The method according to claim 4, wherein the wiring is formed by a sputtering method.

63. (Previously Presented) The method according to claim 4, wherein the wiring comprises aluminum.

64. (Previously Presented) The method according to claim 4, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

65. (Currently Amended) The method according to claim 4, wherein the ~~insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

66. (Currently Amended) The method according to claim 4, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

67. (Currently Amended) The method according to claim 4, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

68. (Previously Presented) The method according to claim 4, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

69. (Previously Presented) The method according to claim 4, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

70. (Previously Presented) The method according to claim 4, wherein the pixel electrode is made of a conductive oxide film.

71. (Previously Presented) The method according to claim 5, wherein the wiring is formed by a sputtering method.

72. (Previously Presented) The method according to claim 5, wherein the wiring comprises

aluminum.

73. (Previously Presented) The method according to claim 5, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

74. (Currently Amended) The method according to claim 5, wherein the ~~insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

75. (Currently Amended) The method according to claim 5, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

76. (Currently Amended) The method according to claim 5, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

77. (Previously Presented) The method according to claim 5, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

78. (Previously Presented) The method according to claim 5, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

79. (Previously Presented) The method according to claim 5, wherein the pixel electrode is made of a conductive oxide film.

80. (Previously Presented) The method according to claim 6, wherein the wiring is formed by a sputtering method.

81. (Previously Presented) The method according to claim 6, wherein the wiring comprises aluminum.

82. (Previously Presented) The method according to claim 6, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

83. (Currently Amended) The method according to claim 6, wherein the ~~insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

84. (Currently Amended) The method according to claim 6, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

85. (Currently Amended) The method according to claim 6, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

86. (Previously Presented) The method according to claim 6, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

87. (Previously Presented) The method according to claim 6, wherein the method further

comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

88. (Previously Presented) The method according to claim 6, wherein the pixel electrode is made of a conductive oxide film.

89. (Previously Presented) The method according to claim 7, wherein the wiring is formed by a sputtering method.

90. (Previously Presented) The method according to claim 7, wherein the wiring comprises aluminum.

91. (Previously Presented) The method according to claim 7, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

92. (Canceled)

93. (Currently Amended) The method according to claim 7, wherein the ~~insulating~~ silicon nitride film has a thickness of 50 to 500nm.

94. (Currently Amended) The method according to claim 7, wherein the ~~insulating~~ silicon nitride film has a thickness of 200 to 300nm.

95. (Previously Presented) The method according to claim 7, wherein the leveling film has a

thickness of 0.1 μm to 1.5 μm.

96. (Previously Presented) The method according to claim 7, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

97. (Previously Presented) The method according to claim 7, wherein the second hole is formed by a dry etching method.

98. (Previously Presented) The method according to claim 7, wherein the pixel electrode is made of a conductive oxide film.

99. (Previously Presented) The method according to claim 8, wherein the wiring is formed by a sputtering method.

100. (Previously Presented) The method according to claim 8, wherein the wiring comprises aluminum.

101. (Previously Presented) The method according to claim 8, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

102. (Canceled)

103. (Currently Amended) The method according to claim 8, wherein the ~~insulating~~ silicon

nitride oxide film has a thickness of 50 to 500nm.

104. (Currently Amended) The method according to claim 8, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

105. (Previously Presented) The method according to claim 8, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

106. (Previously Presented) The method according to claim 8, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

107. (Previously Presented) The method according to claim 8, wherein the second hole is formed by a dry etching method.

108. (Previously Presented) The method according to claim 8, wherein the pixel electrode is made of a conductive oxide film.

109. (Previously Presented) The method according to claim 9, wherein the wiring is formed by a sputtering method.

110. (Previously Presented) The method according to claim 9, wherein the wiring comprises aluminum.

111. (Previously Presented) The method according to claim 9, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

112. (Canceled)

113. (Currently Amended) The method according to claim 9, wherein the ~~first insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

114. (Currently Amended) The method according to claim 9, wherein the ~~first insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

115. (Previously Presented) The method according to claim 9, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

116. (Previously Presented) The method according to claim 9, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

117. (Previously Presented) The method according to claim 9, wherein the second hole is formed by a dry etching method.

118. (Previously Presented) The method according to claim 9, wherein the pixel electrode is made of a conductive oxide film.

119. (Previously Presented) The method according to claim 10, wherein the wiring is formed by a sputtering method.

120. (Previously Presented) The method according to claim 10, wherein the wiring comprises aluminum.

121. (Previously Presented) The method according to claim 10, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

122. (Currently Amended) The method according to claim 10, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

123. (Currently Amended) The method according to claim 10, wherein the ~~passivation~~ silicon nitride film has a thickness of 50 to 500nm.

124. (Currently Amended) The method according to claim 10, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

125. (Previously Presented) The method according to claim 10, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

126. (Previously Presented) The method according to claim 10, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling

film.

127. (Previously Presented) The method according to claim 10, wherein the leveling film comprises an inorganic spin on glass material.

128. (Previously Presented) The method according to claim 10, wherein the pixel electrode is made of a conductive oxide film.

129. (Previously Presented) The method according to claim 31, wherein the wiring is formed by a sputtering method.

130. (Previously Presented) The method according to claim 31, wherein the wiring comprises aluminum.

131. (Previously Presented) The method according to claim 31, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

132. (Currently Amended) The method according to claim 31, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

133. (Currently Amended) The method according to claim 31, wherein the ~~passivation~~ silicon nitride film has a thickness of 50 to 500nm.

134. (Currently Amended) The method according to claim 31, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

135. (Previously Presented) The method according to claim 31, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

136. (Previously Presented) The method according to claim 31, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

137. (Previously Presented) The method according to claim 31, wherein the leveling film comprises an inorganic spin on glass material.

138. (Previously Presented) The method according to claim 31, wherein the pixel electrode is made of a conductive oxide film.

139. (Previously Presented) The method according to claim 33, wherein the wiring is formed by a sputtering method.

140. (Previously Presented) The method according to claim 33, wherein the wiring comprises aluminum.

141. (Previously Presented) The method according to claim 33, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

142. (Currently Amended) The method according to claim 33, wherein the ~~passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

143. (Currently Amended) The method according to claim 33, wherein the ~~passivation~~ silicon nitride film has a thickness of 50 to 500nm.

144. (Currently Amended) The method according to claim 33, wherein the ~~passivation~~ silicon nitride film has a thickness of 200 to 300nm.

145. (Previously Presented) The method according to claim 33, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

146. (Previously Presented) The method according to claim 33, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

147. (Previously Presented) The method according to claim 33, wherein the leveling film comprises an inorganic spin on glass material.

148. (Previously Presented) The method according to claim 33, wherein the pixel electrode is made of a conductive oxide film.

149. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the ~~insulating~~ silicon nitride oxide film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

150. (Previously Presented) The method according to claim 149, wherein the wiring is formed by a sputtering method.

151. (Previously Presented) The method according to claim 149, wherein the wiring comprises aluminum.

152. (Previously Presented) The method according to claim 149, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

153. (Currently Amended) The method according to claim 149, wherein the ~~insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display

device is a liquid crystal display device or an electro luminescence display device.

154. (Currently Amended) The method according to claim 149, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

155. (Currently Amended) The method according to claim 149, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

156. (Previously Presented) The method according to claim 149, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

157. (Previously Presented) The method according to claim 149, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

158. (Previously Presented) The method according to claim 149, wherein the leveling film comprises an inorganic spin on glass material.

159. (Previously Presented) The method according to claim 149, wherein the pixel electrode is made of a conductive oxide film.

160. (Previously Presented) The method according to claim 149, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

161. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a <u>first</u> hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ <u>a silicon nitride oxide</u> film covering a surface of the wiring;

forming a leveling film formed by a spin coating method on the ~~insulating~~ <u>silicon nitride oxide</u> film; <u>and</u>

forming a pixel electrode over the leveling film <u>connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film</u>~~; and~~

~~forming an electro luminescence layer over the pixel electrode~~.

162. (Previously Presented) The method according to claim 161, wherein the wiring is formed by a sputtering method.

163. (Previously Presented) The method according to claim 161, wherein the wiring comprises aluminum.

164. (Previously Presented) The method according to claim 161, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

165. (Currently Amended) The method according to claim 161, wherein the ~~insulating film is~~

~~made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

166. (Currently Amended) The method according to claim 161, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

167. (Currently Amended) The method according to claim 161, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

168. (Previously Presented) The method according to claim 161, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

169. (Previously Presented) The method according to claim 161, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

170. (Previously Presented) The method according to claim 161, wherein the leveling film comprises an inorganic spin on glass material.

171. (Previously Presented) The method according to claim 161, wherein the pixel electrode is made of a conductive oxide film.

172. (Previously Presented) The method according to claim 161, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer,

and a projector.

173. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming ~~an insulating~~ a silicon nitride oxide film deposited on the wiring;

forming a leveling film formed by a spin coating method on the ~~insulating~~ silicon nitride oxide film; and

forming a pixel electrode over the leveling film connecting to the wiring through a second hole formed in the silicon nitride oxide film and the leveling film; ~~and~~

~~forming an electro luminescence layer over the pixel electrode~~.

174. (Previously Presented) The method according to claim 173, wherein the wiring is formed by a sputtering method.

175. (Previously Presented) The method according to claim 173, wherein the wiring comprises aluminum.

176. (Previously Presented) The method according to claim 173, wherein the wiring is a three-layered laminate film containing a first titanium film, an aluminum film and a second titanium film.

177. (Currently Amended) The method according to claim 173, wherein the ~~insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film~~ display device is a liquid crystal display device or an electro luminescence display device.

178. (Currently Amended) The method according to claim 173, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 50 to 500nm.

179. (Currently Amended) The method according to claim 173, wherein the ~~insulating~~ silicon nitride oxide film has a thickness of 200 to 300nm.

180. (Previously Presented) The method according to claim 173, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

181. (Previously Presented) The method according to claim 173, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

182. (Previously Presented)The method according to claim 173, wherein the leveling film comprises an inorganic spin on glass material.

183. (Previously Presented) The method according to claim 173, wherein the pixel electrode is made of a conductive oxide film.

184. (Previously Presented) The method according to claim 173, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.